

## FJNS3205R

### Switching Application (Bias Resistor Built In)

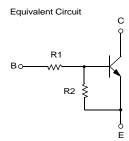
- Switching circuit, Inverter, Interface circuit, Driver Circuit
- Built in bias Resistor ( $R_1$ =4.7 $K\Omega$ ,  $R_2$ =10 $K\Omega$ )
- Complement to FJNS4205R



## **NPN Epitaxial Silicon Transistor**

## **Absolute Maximum Ratings** $T_a$ =25°C unless otherwise noted

Symbol	Parameter	Value	Units
V <sub>CBO</sub>	Collector-Base Voltage	50	V
V <sub>CEO</sub>	Collector-Emitter Voltage	50	V
V <sub>EBO</sub>	Emitter-Base Voltage	10	V
I <sub>C</sub>	Collector Current	100	mA
P <sub>C</sub>	Collector Power Dissipation	300	mW
T <sub>J</sub>	Junction Temperature	150	°C
T <sub>STG</sub>	Storage Temperature	-55 ~ 150	°C



### Electrical Characteristics T<sub>a</sub>=25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
BV <sub>CBO</sub>	Collector-Base Breakdown Voltage	$I_{C}=10\mu A, I_{E}=0$	50			V
BV <sub>CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> =100μA, I <sub>B</sub> =0	50			V
I <sub>CBO</sub>	Collector Cut-off Current	$V_{CB}$ =40V, $I_{E}$ =0			0.1	μΑ
h <sub>FE</sub>	DC Current Gain	V <sub>CE</sub> =5V, I <sub>C</sub> =5mA	30			
V <sub>CE</sub> (sat)	Collector-Emitter Saturation Voltage	I <sub>C</sub> =10mA, I <sub>B</sub> =0.5mA			0.3	V
C <sub>ob</sub>	Output Capacitance	V <sub>CE</sub> =10V, I <sub>C</sub> =5mA f=1MHz		3.7		pF
f <sub>T</sub>	Current Gain Bandwidth Product	V <sub>CE</sub> =10V, I <sub>C</sub> =5mA		250		MHz
V <sub>I</sub> (off)	Input Off Voltage	V <sub>CE</sub> =5V, I <sub>C</sub> =100μA	0.3			V
V <sub>I</sub> (on)	Input On Voltage	$V_{CE}$ =0.3V, $I_{C}$ =20mA			2.5	V
R <sub>1</sub>	Input Resistor		3.2	4.7	6.2	ΚΩ
R <sub>1</sub> /R <sub>2</sub>	Resistor Ratio		0.42	0.47	0.52	

# **Typical Characteristics**

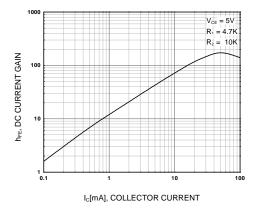


Figure 1. DC current Gain

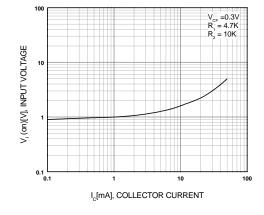


Figure 2. Input On Voltage

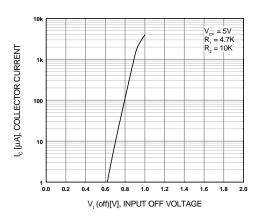


Figure 3. Input Off Voltage

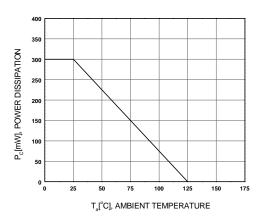
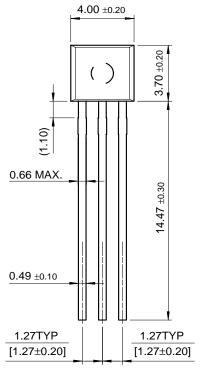
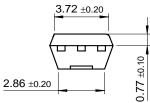


Figure 4. Power Derating

**TO-92S** 







Dimensions in Millimeters

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